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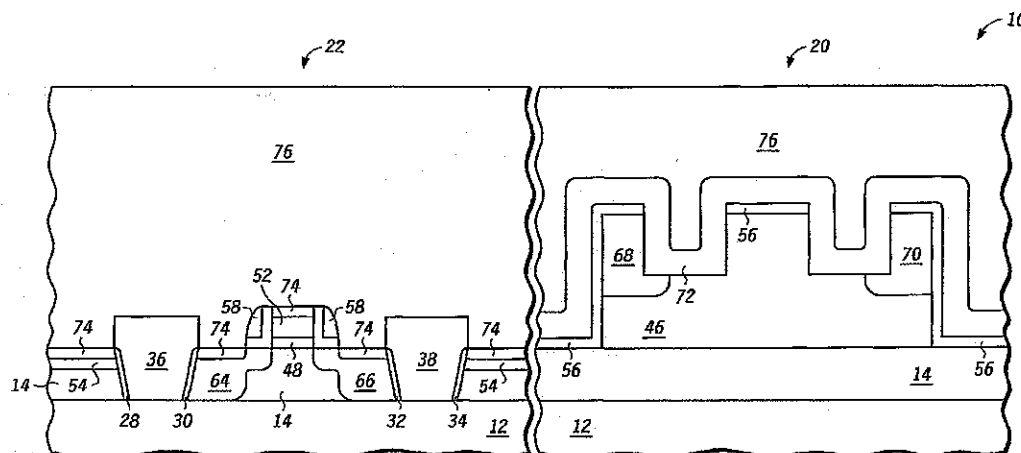
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(54) Title: METHOD OF INTEGRATING OPTICAL DEVICES AND ELECTRONIC DEVICES ON AN INTEGRATED CIRCUIT



(57) Abstract: A method for integrating an optical device and an electronic device on a semiconductor substrate comprises forming openings (24, 26) within an active semiconductor layer (14) in a first region (22) of the semiconductor substrate, wherein the first region corresponds to an electronic device portion and a second region (20) corresponds to an optical device portion. A semiconductor layer (46) is epitaxially grown overlying an exposed active semiconductor layer (14) in the second region (20), the epitaxially grown semiconductor layer (46) corresponding to an optical device region. At least a portion of an electronic device is formed on the active semiconductor layer (14) within the electronic device portion (22) of the semiconductor substrate. The method further includes forming openings (60, 62) within the epitaxially grown semiconductor layer (46) of the optical device portion (20) of the semiconductor substrate, wherein the openings (60, 62) define one or more features of an optical device.